| Reg. No.: |
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Question Paper Code: 21010

B.E. / B.Tech. DEGREE EXAMINATION, MAY 2014.

Second Semester

Electronics and Communication Engineering

01UEC207 - ELECTRONIC DEVICES

(Regulation 2013)

Duration: Three hours Maximum: 100 Marks

Answer ALL Questions.

PART A -
$$(10 \times 2 = 20 \text{ Marks})$$

- 1. What is meant by doping in a semiconductor?
- 2. Define the term conductivity in a semiconductor.
- 3. Define peak inverse voltage in a PN Junction Diode.
- 4. Write short note on avalanche breakdown.
- 5. Discuss the relation between α and β .
- 6. Write short note on leakage current in Common Base configuration.
- 7. List out the differences between JFET and BJT.
- 8. Define Pinch off voltage (Vp).
- 9. What are the advantages of TRIAC over SCR?
- 10. List out any four applications of Photodiode.

PART - B (5 x 16 = 80 Marks)

| 11. | (a) | What is drift current? Derive the expression for drift current and diffusion current in semiconductors. (16) | |
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| Or | | | |
| | (b) | (i) Explain the classification of solids based on energy band. (8) | |
| | | (ii) Derive the conductivity equation for an N type and P type Semiconductor. (8) | |
| 12. | (a) | Explain the working of a PN junction diode under various biasing conditions using the relevant circuit sketch. (16) | |
| Or | | | |
| | (b) | Explain the construction and working of Half wave and full wave rectifiers with resistive load. (16) | |
| 13. | (a) | With neat diagram explain the operation and Input and Output characteristic of CE configuration. (16) | |
| Or | | | |
| | (b) | (i) Explain the switching characteristics of BJT. (8) | |
| | | (ii) Compare the characteristics of CE, CB and CC configurations. (8) | |
| 14. | (a) | Explain the construction, working and operating characteristics of N-Channel JFETs with relevant diagrams. Give the application of JFET. (16) | |
| Or | | | |
| | (b) | (i) Compare the depletion mode and enhancement mode of MOSFET. (4) | |
| | | (ii) Explain the Principle of operation of Enhancement N-Chennal MOSFET and draw its drain characteristics. (12) | |
| 15. | (a) | With neat diagram explain the constructional details and working principle of SCR. (16) | |
| Or | | | |
| | (b) | With relevant sketches explain the construction, working and characteristics of UJT. (16) | |